

SEMITOP[®] 3

IGBT Module

SK45GH063

Preliminary Data

Features

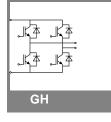
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchtrough IGBT)
- High short circuit capability
- Low tail current with low
- temperature dependenceUL recognized, file no. E63532

Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Absolute Maximum Ratings T _s = 25 °C, unless otherwise specified							
Symbol	Conditions		Values	Units			
IGBT							
V _{CES}	T _j = 25 °C		600	V			
I _C	T _j = 125 °C	T _s = 25 °C	45	А			
		T _s = 80 °C	30	А			
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		100	А			
V _{GES}			± 20	V			
t _{psc}	$V_{CC} = 300 \text{ V}; \text{ V}_{GE} \le 20 \text{ V}; \\ \text{V}_{CES} < 600 \text{ V}$	T _j = 125 °C	10	μs			
Inverse	Diode						
I _F	T _j = 150 °C	T _s = 25 °C	57	А			
		T _s = 80 °C	38	А			
I _{FRM}	I _{FRM} = 2 x I _{Fnom}		100	А			
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	440	А			
Module	_						
I _{t(RMS)}				А			
T _{vj}			-40 +150	°C			
T _{stg}			-40 +125	°C			
V _{isol}	AC, 1 min.		2500	V			

Characteristics T _s =			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$		4,5	5,5	6,5	V	
I _{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T _j = 25 °C			0,15	mA	
		T _j = 125 °C				mA	
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 25 °C			120	nA	
		T _j = 125 °C				nA	
V _{CE0}		T _j = 25 °C		1		V	
		T _j = 125 °C		1,1		V	
r _{CE}	V _{GE} = 15 V	T _j = 25°C		20		mΩ	
		T _j = 125°C				mΩ	
V _{CE(sat)}	I _{Cnom} = 50 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		2,1	2,5	V	
		T _j = 125°C _{chiplev.}				V	
C _{ies}				2,2		nF	
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz				nF	
C _{res}				0,2		nF	
Q _G	V _{GE} = 0 20 V			155		nC	
t _{d(on)}				45		ns	
t, F	R_{Gon} = 22 Ω	$V_{CC} = 300V$		35		ns	
Ė _{on}	D = 00 0	I _C = 30A		1,4		mJ	
^L d(off)	$R_{Goff} = 22 \Omega$	T _j = 125 °C V _{GE} =±15V		250 25		ns ns	
t _f E _{off}		GE-TION		1,2		mJ	
R _{th(j-s)}	per IGBT	L		,	1	K/W	



13-02-2007 DIL



SEMITOP[®] 3

IGBT Module

SK45GH063

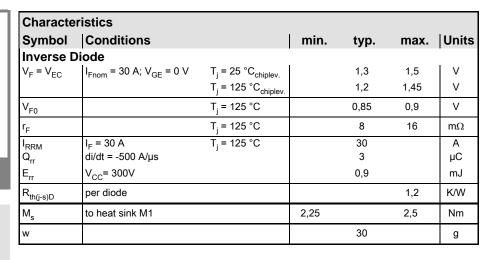
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchtrough IGBT)
- High short circuit capability
- . Low tail current with low
- temperature dependence
- UL recognized, file no. E63532

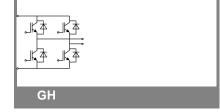
Typical Applications*

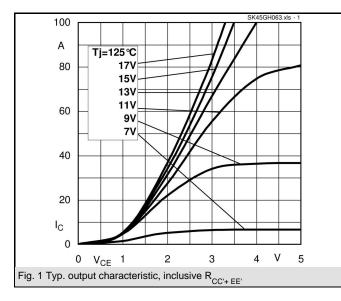
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

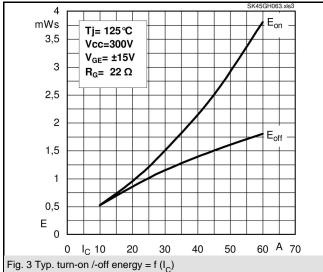


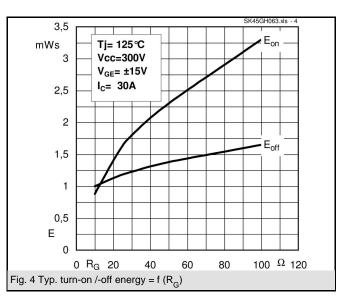
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

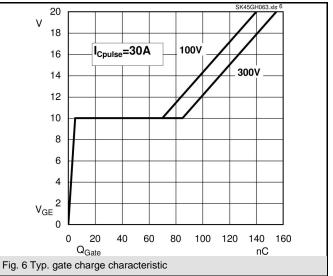
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.





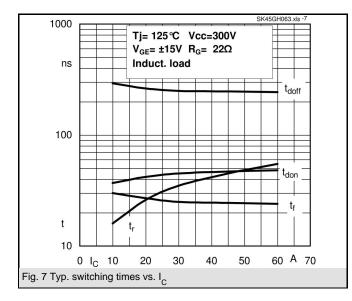


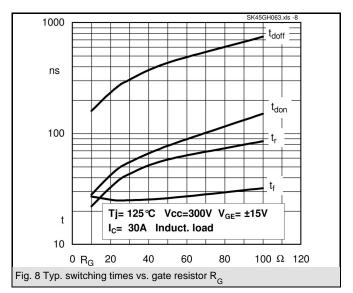


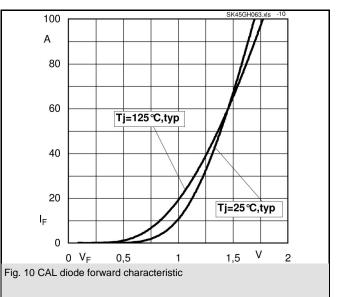


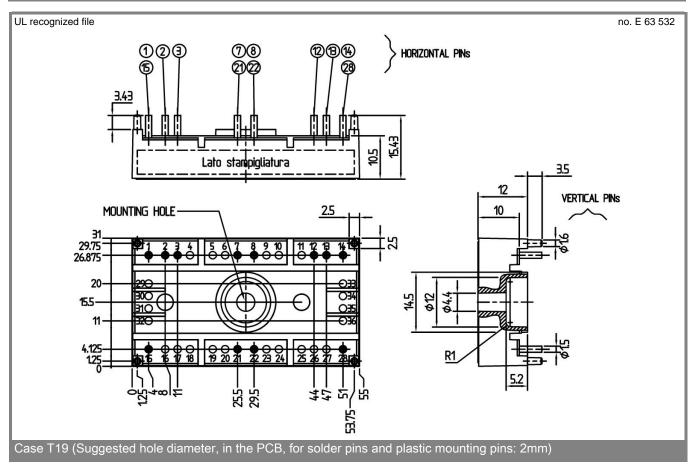
3

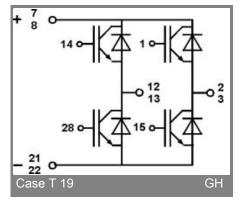
13-02-2007 DIL











5